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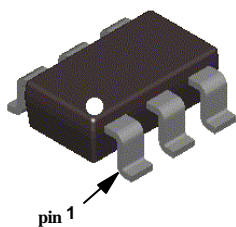
## FDC6324L Integrated Load Switch

### General Description

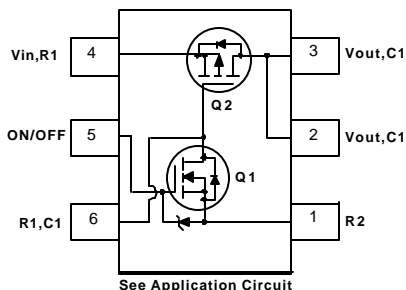
These Integrated Load Switches are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage high side load switch application where low conduction loss and ease of driving are needed.

### Features

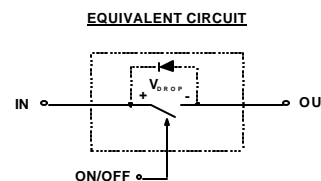
- $V_{DROD}=0.2V$  @  $V_{IN}=12V$ ,  $I_L=1A$ ,  $V_{ON/OFF}=1.5$  to  $8V$   
 $V_{DROD}=0.3V$  @  $V_{IN}=5V$ ,  $I_L=1A$ ,  $V_{ON/OFF}=1.5$  to  $8V$ .
- High density cell design for extremely low on-resistance.
- $V_{ON/OFF}$  Zener protection for ESD ruggedness. >6KV Human Body Model.
- SuperSOT™-6 package design using copper lead frame for superior thermal and electrical capabilities.



SuperSOT™-6



See Application Circuit



### Absolute Operating Range $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDC6324L	Units
$V_{IN}$	Input Voltage Range	3 - 20	V
$V_{ON/OFF}$	ON/OFF Voltage Range	1.5 - 8	V
$I_L$	Load Current @ $V_{DROD}=0.5V$ - Continuous (Note 1)	1.5	A
	- Pulsed (Note 1 & 3)	2.5	
$P_D$	Maximum Power Dissipation (Note 2a)	0.7	W
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf/1500Ohm)	6	kV

### THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2a)	180	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	60	$^\circ\text{C/W}$

### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
I <sub>FL</sub>	Forward Leakage Current	V <sub>IN</sub> = 20 V, V <sub>ON/OFF</sub> = 0 V			1	μA
I <sub>RL</sub>	Reverse Leakage Current	V <sub>IN</sub> = -20 V, V <sub>ON/OFF</sub> = 0 V			-1	μA
<b>ON CHARACTERISTICS</b> (Note 3)						
V <sub>IN</sub>	Input Voltage		3		20	V
V <sub>ON/OFF</sub>	On/Off Voltage		1.5		8	V
V <sub>DROP</sub>	Conduction Voltage Drop @ 1A	V <sub>IN</sub> = 10 V, V <sub>ON/OFF</sub> = 3.3V		0.135	0.2	V
		V <sub>IN</sub> = 5 V, V <sub>ON/OFF</sub> = 3.3 V		0.215	0.3	
I <sub>L</sub>	Load Current	V <sub>DROP</sub> = 0.2 V, V <sub>IN</sub> = 10 V, V <sub>ON/OFF</sub> = 3.3 V	1			A
		V <sub>DROP</sub> = 0.3 V, V <sub>IN</sub> = 5 V, V <sub>ON/OFF</sub> = 3.3 V	1			

Notes:

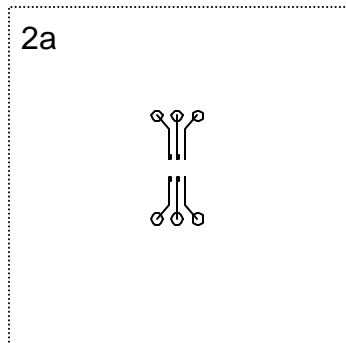
1. V<sub>IN</sub> = 20V, V<sub>ON/OFF</sub> = 8V, V<sub>DROP</sub> = 0.5V, T<sub>A</sub> = 25°C

2. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.

$$P_D(t) = \frac{T_j - T_A}{R_{\theta J A}(t)} = \frac{T_j - T_A}{R_{\theta J C} + R_{\theta C A}(t)} = I_D^2(t) \times R_{DS(ON)} @ T_j$$

Typical R<sub>θJA</sub> for single device operation using the board layouts shown below on FR-4 PCB in still air environment

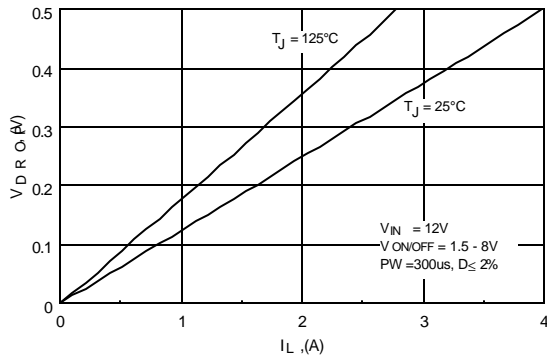
a. 180°C/W when mounted on a 2oz minimum copper pad.



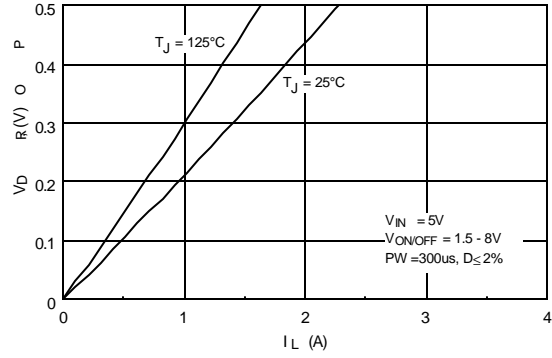
Scale 1 : 1 on letter size paper

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

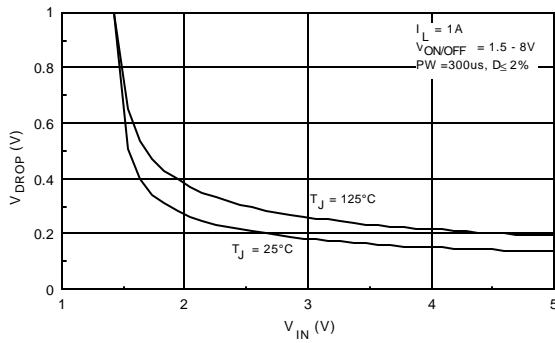
**Typical Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)



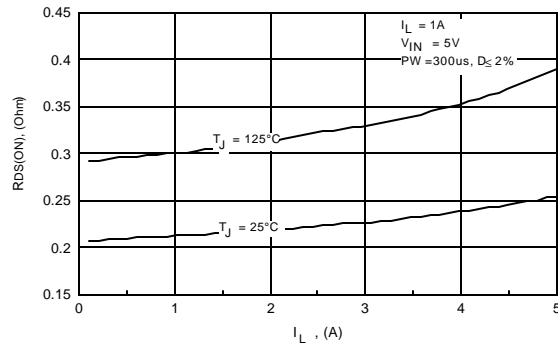
**Figure 1.**  $V_{\text{DROP}}$  Versus  $I_L$  at  $V_{\text{IN}}=12\text{V}$ .



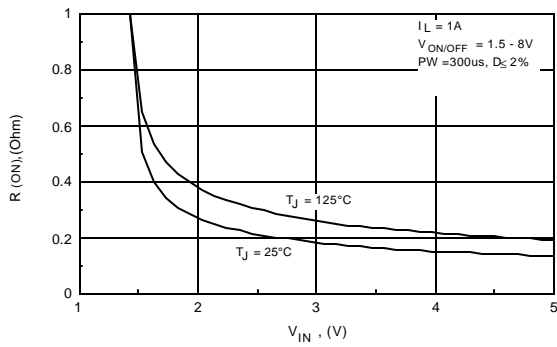
**Figure 2.**  $V_{\text{DROP}}$  Versus  $I_L$  at  $V_{\text{IN}}=5.0\text{V}$ .



**Figure 3.**  $V_{\text{DROP}}$  Versus  $V_{\text{IN}}$  at  $I_L=1\text{A}$ .

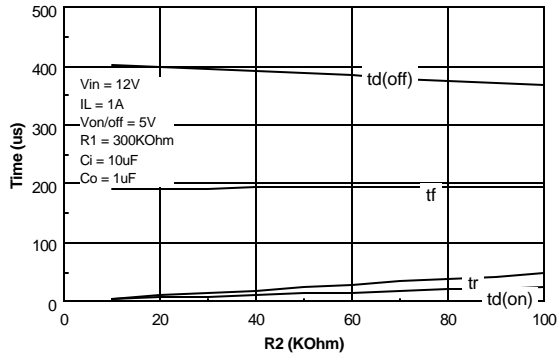


**Figure 4.**  $R_{\text{DS(ON)}}$  Versus  $I_L$  at  $V_{\text{IN}}=5.0\text{V}$ .

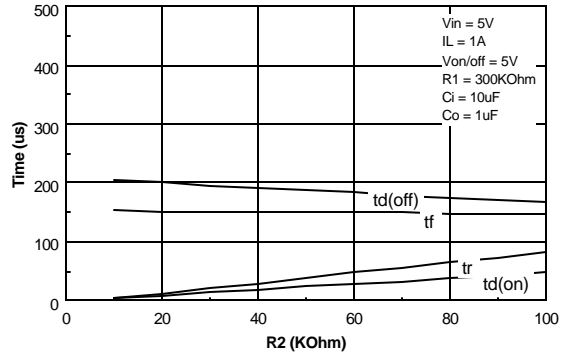


**Figure 5.** On Resistance Variation with Input Voltage.

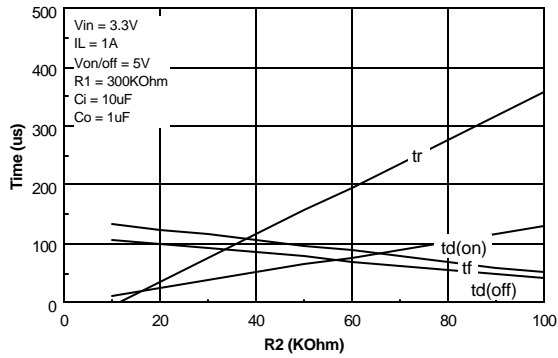
**Typical Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise noted)



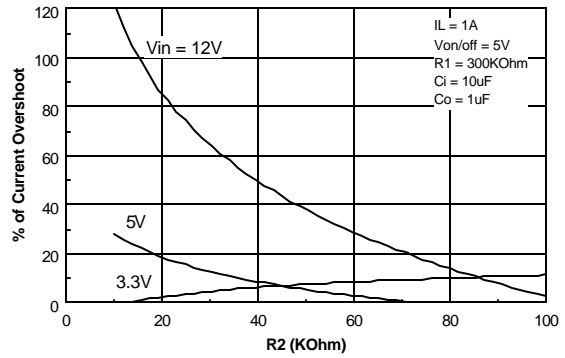
**Figure 6. Switching Variation with R2 at  $V_{in} = 12\text{V}$  and  $R_1 = 300\text{K}\Omega$ .**



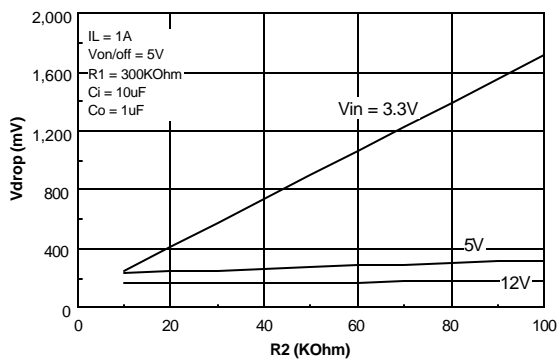
**Figure 7. Switching Variation with R2 at  $V_{in} = 5\text{V}$  and  $R_1 = 300\text{K}\Omega$ .**



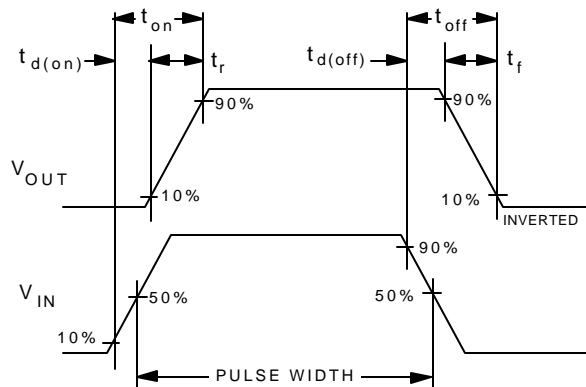
**Figure 8. Switching Variation with R2 at  $V_{in} = 3.3\text{V}$  and  $R_1 = 300\text{K}\Omega$ .**



**Figure 9. % of Current Overshoot Variation with  $V_{in}$  and R2.**

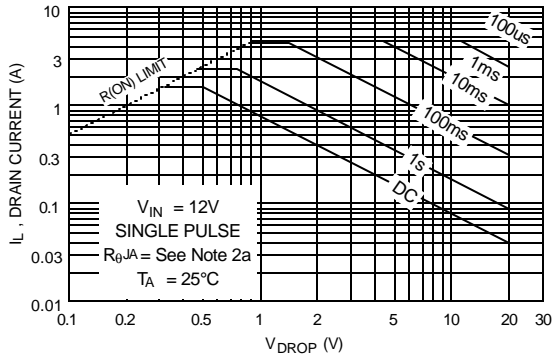


**Figure 10. Vdrop Variation with  $V_{in}$  and R2.**

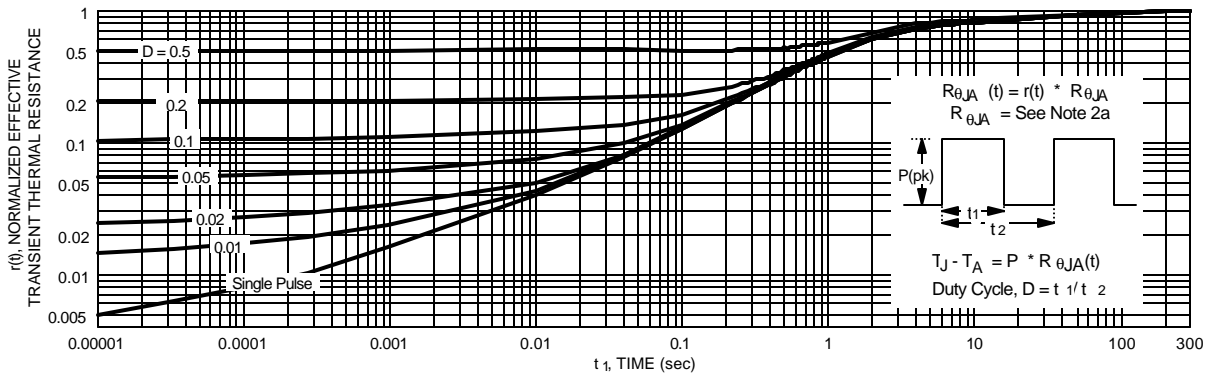


**Figure 11. Switching Waveforms.**

**Typical Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise noted )



**Figure 12. Safe Operating Area.**

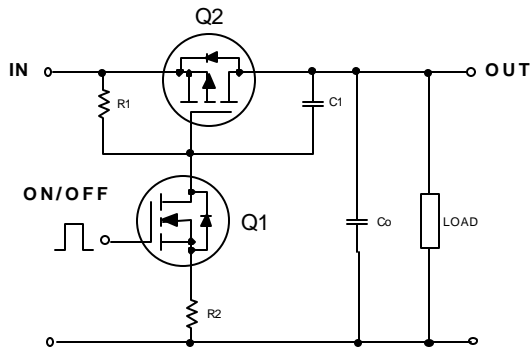


**Figure 13. Transient Thermal Response Curve.**

Note: Thermal characterization performed on the conditions described in Note 2a. Transient thermal response will change depends on the circuit board

## FDC6324L Load Switch Application

### APPLICATION CIRCUIT



### General Description

This device is particularly suited for computer peripheral switching applications where 20V input and 1A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOT™-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N-Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N-Channel device the driving stage is simplified.

### Component Values

R1	Typical 10k - 1M $\Omega$	
R2	Typical 0 - 10k $\Omega$	(optional)
C1	Typical 1000pF	(optional)

### Design Notes

- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in the case the output capacitance Co is small.
- $R2 \leq$  should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation
$$I_{BIAS\_LOSS} = \frac{V_{in}}{R1 + R2}$$
when the switch is ON.  $I_{BIAS\_LOSS}$  can be minimized by large R1.
- R2 and  $C_{RSS}$  of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C1 can be added externally to slow down the turn on.

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